

NTB25P06T4G Datasheet

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DiGi Electronics Part Number	NTB25P06T4G-DG
Manufacturer	onsemi
Manufacturer Product Number	NTB25P06T4G
Description	MOSFET P-CH 60V 27.5A D2PAK
Detailed Description	P-Channel 60 V 27.5A (Ta) 120W (Tj) Surface Mount D2PAK



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DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

NTB25P06T4G

Series:

-

FET Type:

P-Channel

Drain to Source Voltage (Vdss):

60 V

Drive Voltage (Max Rds On, Min Rds On):

10V

Vgs(th) (Max) @ Id:

4V @ 250 μ A

Vgs (Max):

\pm 15V

FET Feature:

-

Operating Temperature:

-55°C ~ 175°C (Tj)

Supplier Device Package:

D2PAK

Base Product Number:

NTB25

Manufacturer:

onsemi

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

27.5A (Ta)

Rds On (Max) @ Id, Vgs:

82mOhm @ 25A, 10V

Gate Charge (Qg) (Max) @ Vgs:

50 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

1680 pF @ 25 V

Power Dissipation (Max):

120W (Tj)

Mounting Type:

Surface Mount

Package / Case:

TO-263-3, D2PAK (2 Leads + Tab), TO-263AB

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

MOSFET - P-Channel, D²PAK

-60 V, -27.5 A

NTB25P06, NVB25P06

Designed for low voltage, high speed switching applications and to withstand high energy in the avalanche and commutation modes.

Features

- AEC Q101 Qualified – NVB25P06
- These Devices are Pb-Free and are RoHS Compliant

Typical Applications

- PWM Motor Controls
- Power Supplies
- Converters
- Bridge Circuits

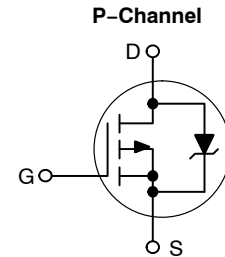
MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	-60	V
Gate-to-Source Voltage	V _{GS}	± 15	V
– Continuous	V _{GSM}	± 20	Vpk
– Non-Repetitive (t _p ≤ 10 ms)			
Drain Current	I _D	27.5	A
– Continuous @ T _A = 25°C	I _{DM}	80	Apk
– Single Pulse (t _p ≤ 10 μs)			
Total Power Dissipation @ T _A = 25°C	P _D	120	W
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +175	°C
Single Pulse Drain-to-Source Avalanche Energy – Starting T _J = 25°C (V _{DD} = 25 V, V _{GS} = 10 V, I _{L(pk)} = 20 A, L = 3 mH, R _G = 25 Ω)	E _{AS}	600	mJ
Thermal Resistance			°C/W
– Junction-to-Case	R _{θJC}	1.25	
– Junction-to-Ambient (Note 1)	R _{θJA}	46.8	
– Junction-to-Ambient (Note 2)	R _{θJA}	63.2	
Maximum Lead Temperature for Soldering Purposes, (1/8" from case for 10 s)	T _L	260	°C

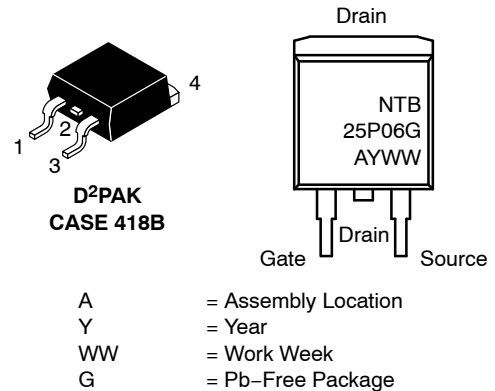
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. When surface mounted to an FR4 board using 1" pad size (Cu Area 1.127 in²).
2. When surface mounted to an FR4 board using the minimum recommended pad size (Cu Area 0.412 in²).

V _{(BR)DSS}	R _{DS(on)} TYP	I _D MAX
-60 V	65 mΩ @ -10 V	-27.5 A



MARKING DIAGRAM & PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping [†]
NTB25P06T4G	D ² PAK (Pb-Free)	800 / Tape & Reel
NVB25P06T4G	D ² PAK (Pb-Free)	800 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTB25P06, NVB25P06**ELECTRICAL CHARACTERISTICS** ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (Note 3) ($V_{GS} = 0\text{ V}$, $I_D = -250\ \mu\text{A}$) (Positive Temperature Coefficient)	$V_{(BR)DSS}$	-60 -	- 64	- -	V $\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current ($V_{GS} = 0\text{ V}$, $V_{DS} = -60\text{ V}$, $T_J = 25^\circ\text{C}$) ($V_{GS} = 0\text{ V}$, $V_{DS} = -60\text{ V}$, $T_J = 150^\circ\text{C}$)	I_{DSS}	- -	- -	-10 -100	μA
Gate-Body Leakage Current ($V_{GS} = \pm 15\text{ V}$, $V_{DS} = 0\text{ V}$)	I_{GSS}	-	-	± 100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = -250\ \mu\text{A}$) (Negative Threshold Temperature Coefficient)	$V_{GS(th)}$	-2.0 -	-2.8 6.2	-4.0 -	V $\text{mV}/^\circ\text{C}$
Static Drain-Source On-State Resistance ($V_{GS} = -10\text{ V}$, $I_D = -12.5\text{ A}$) ($V_{GS} = -10\text{ V}$, $I_D = -25\text{ A}$)	$R_{DS(on)}$	- -	0.065 0.070	0.075 0.082	Ω
Forward Transconductance ($V_{DS} = -10\text{ V}$, $I_D = -12.5\text{ A}$)	gFS	-	13	-	Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	$(V_{DS} = -25\text{ V}$, $V_{GS} = 0\text{ V}$, $F = 1.0\text{ MHz}$)	C_{iss}	-	1200	1680	pF
Output Capacitance		C_{oss}	-	345	480	
Reverse Transfer Capacitance		C_{rss}	-	90	180	

SWITCHING CHARACTERISTICS (Notes 3 & 4)

Turn-On Delay Time	$(V_{DD} = -30\text{ V}$, $I_D = -25\text{ A}$, $V_{GS} = -10\text{ V}$, $R_G = 9.1\ \Omega$)	$t_{d(on)}$	-	14	24	ns
Rise Time		t_r	-	72	118	ns
Turn-Off Delay Time		$t_{d(off)}$	-	43	68	ns
Fall Time		t_f	-	190	320	ns
Gate Charge	$(V_{DS} = -48\text{ V}$, $I_D = -25\text{ A}$, $V_{GS} = -10\text{ V}$)	Q_T	-	33	50	nC
		Q_1	-	6.5	-	
		Q_2	-	15	-	

BODY-DRAIN DIODE RATINGS (Note 3)

Diode Forward On-Voltage	$(I_S = -25\text{ A}$, $V_{GS} = 0\text{ V}$) $(I_S = -25\text{ A}$, $V_{GS} = 0\text{ V}$, $T_J = 150^\circ\text{C}$)	V_{SD}	- -	-1.8 -1.4	-2.5 -	V
Reverse Recovery Time	$(I_S = -25\text{ A}$, $V_{GS} = 0\text{ V}$, $di_S/dt = 100\text{ A}/\mu\text{s}$)	t_{rr}	-	70	-	ns
		t_a	-	50	-	
		t_b	-	20	-	
Reverse Recovery Stored Charge		Q_{RR}	-	0.2	-	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Indicates Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

4. Switching characteristics are independent of operating junction temperatures.

NTB25P06, NVB25P06

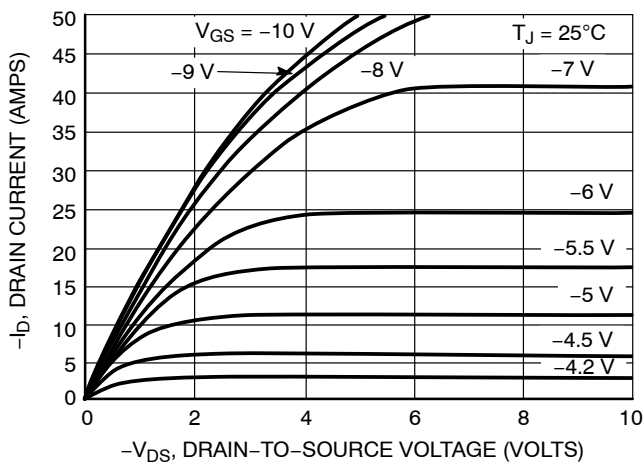


Figure 1. On-Region Characteristics

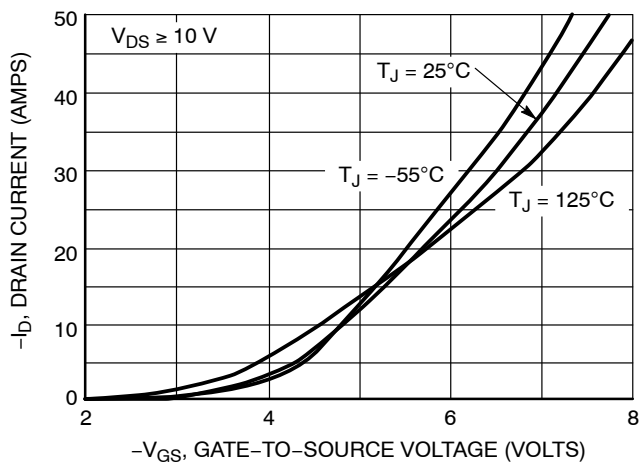


Figure 2. Transfer Characteristics

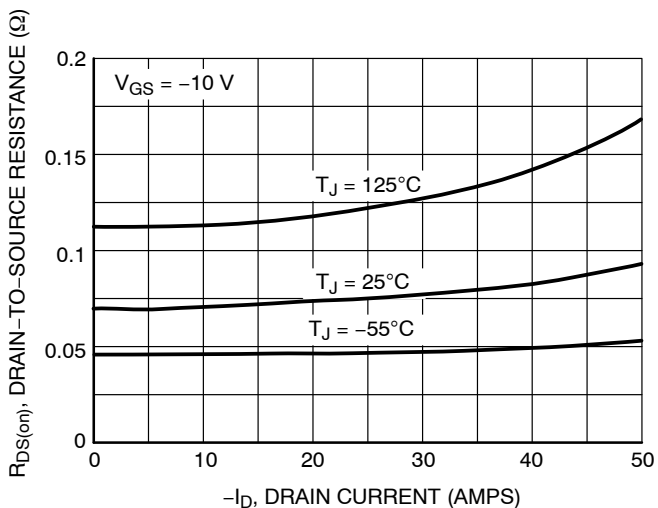


Figure 3. On-Resistance vs. Drain Current and Temperature

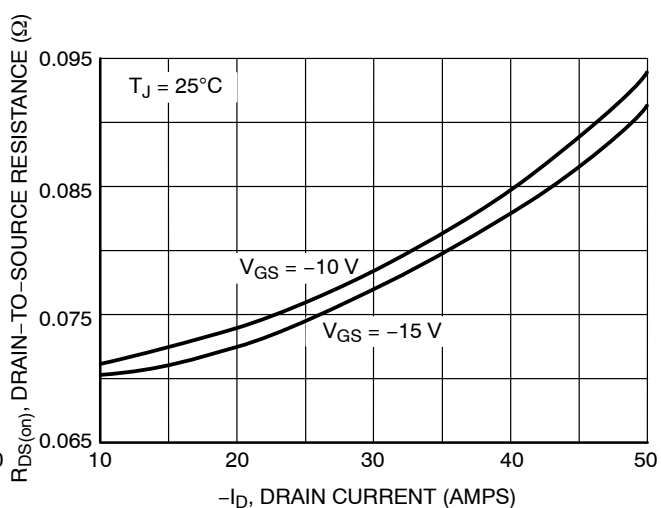


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

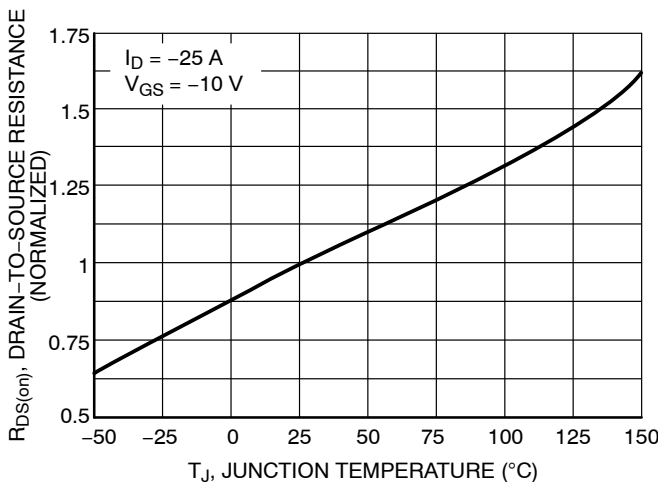


Figure 5. On-Resistance Variation with Temperature

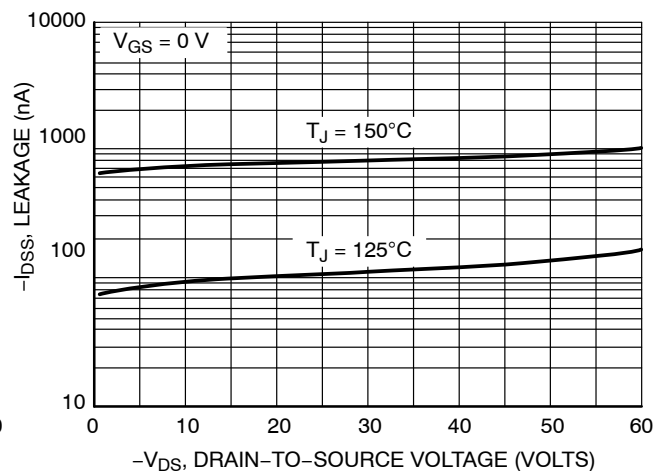


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTB25P06, NVB25P06

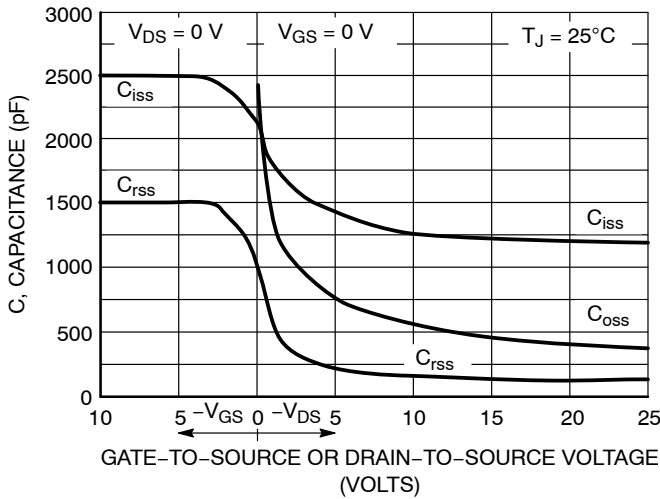


Figure 7. Capacitance Variation

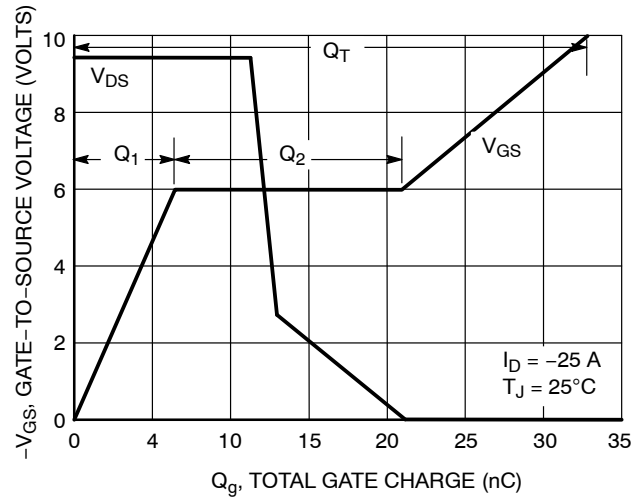


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

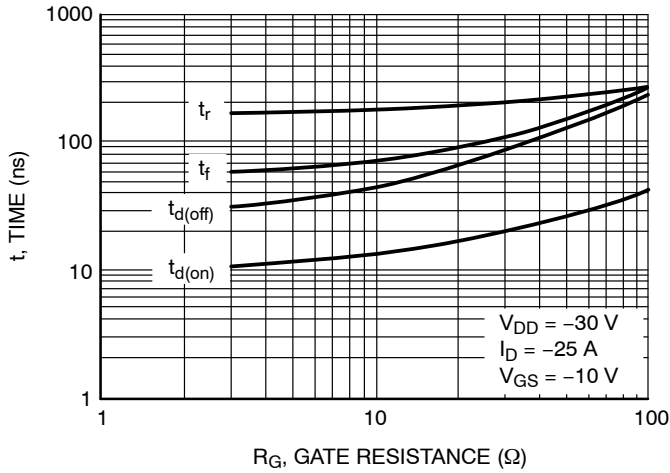


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

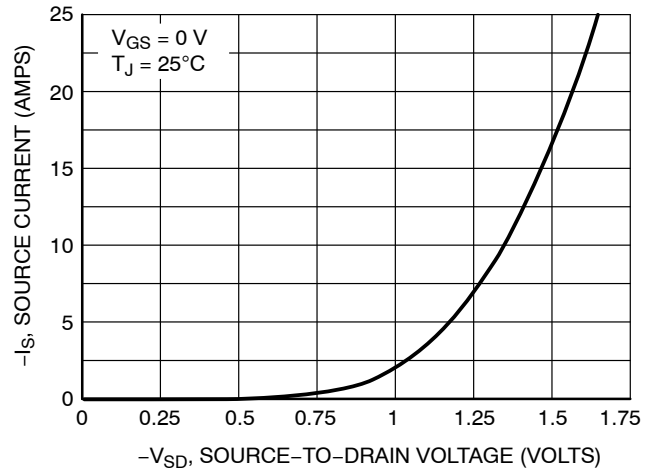


Figure 10. Diode Forward Voltage vs. Current

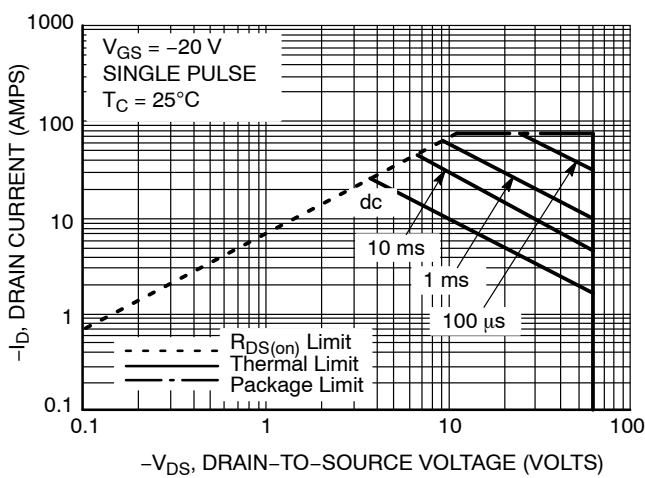


Figure 11. Maximum Rated Forward Biased Safe Operating Area

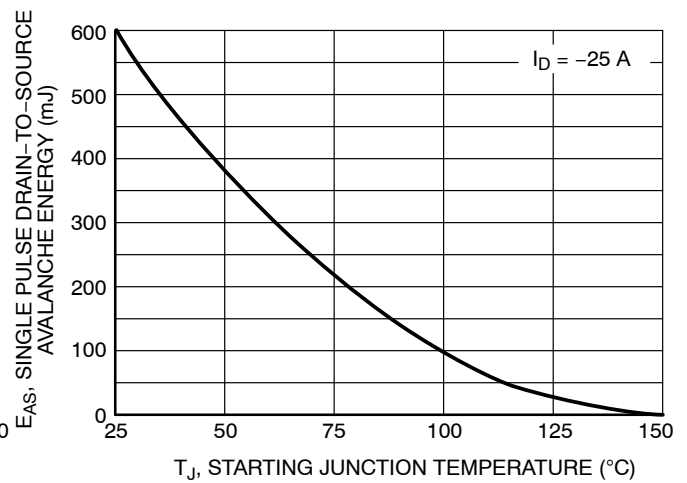
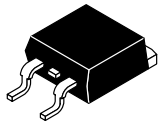


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature



**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



D²PAK 3
CASE 418B-04
ISSUE L

DATE 17 FEB 2015

SCALE 1:1

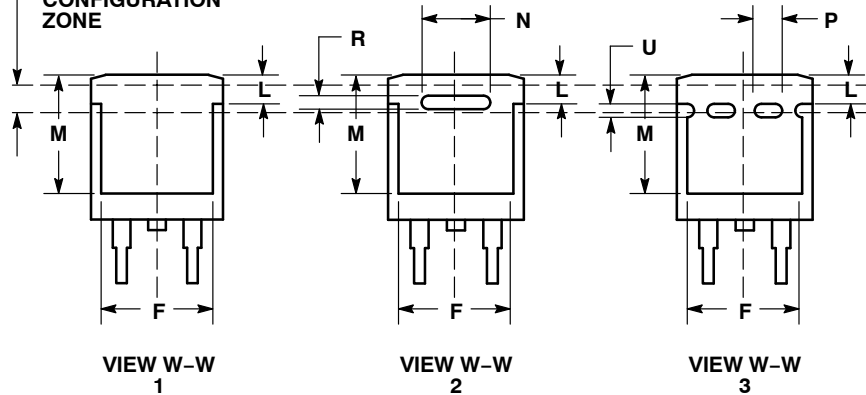


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197	REF	5.00	REF
P	0.079	REF	2.00	REF
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

VARIABLE CONFIGURATION ZONE



- | | | | | | |
|--|---|---|--|---|--|
| STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR | STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN | STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE | STYLE 4:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR | STYLE 5:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE | STYLE 6:
PIN 1. NO CONNECT
2. CATHODE
3. ANODE
4. CATHODE |
|--|---|---|--|---|--|

MARKING INFORMATION AND FOOTPRINT ON PAGE 2

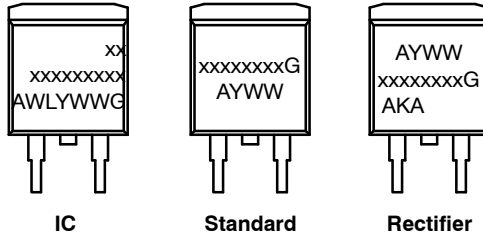
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D²PAK 3
CASE 418B-04
ISSUE L

DATE 17 FEB 2015

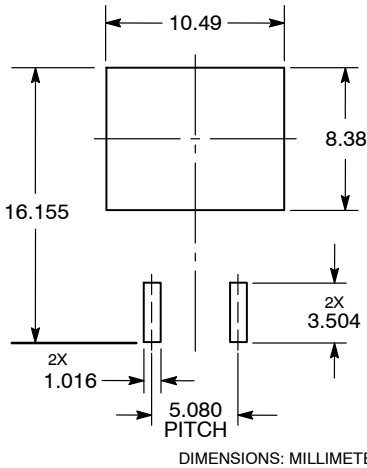
GENERIC MARKING DIAGRAM*



- xx = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package
- AKA = Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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